

Transistor

Panasonic

2SB789, 2SB789A

Silicon PNP epitaxial planer type

For low-frequency driver amplification

Complementary to 2SD968 and 2SD968A

Features

- High collector to emitter voltage V_{CEO} .
- Large collector power dissipation P_C .

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	2SB789	-100	V
	2SB789A	-120	
Collector to emitter voltage	2SB789	-100	V
	2SB789A	-120	
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-1	A
Collector current	I_C	-0.5	A
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

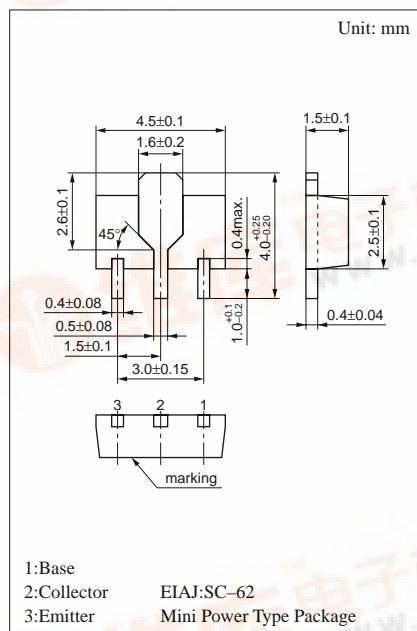
* Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to emitter voltage	2SB789	$I_C = -100\mu A, I_B = 0$	-100			V
	2SB789A		-120			
Collector to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -10V, I_C = -150mA$	90		220	
	h_{FE2}	$V_{CE} = -5V, I_C = -500mA$	50			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.2	-0.6	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			30	pF

* h_{FE1} Rank classification

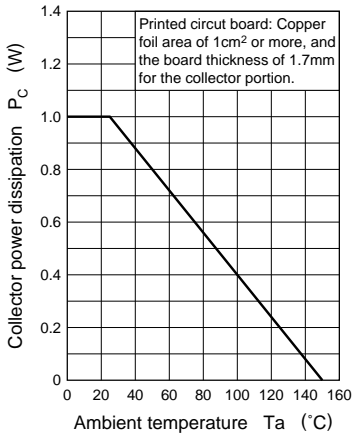
Rank	Q	R
h_{FE1}	90 ~ 155	130 ~ 220
Marking	2SB789	DQ
Symbol	2SB789A	EQ
		DR
		ER



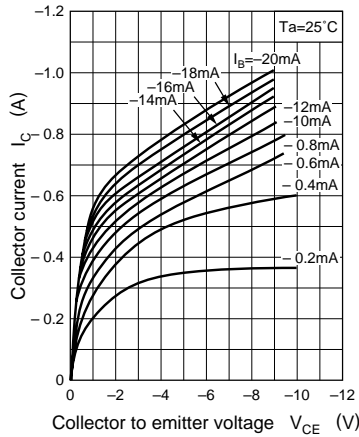
Marking symbol : D(2SB789)
E(2SB789A)



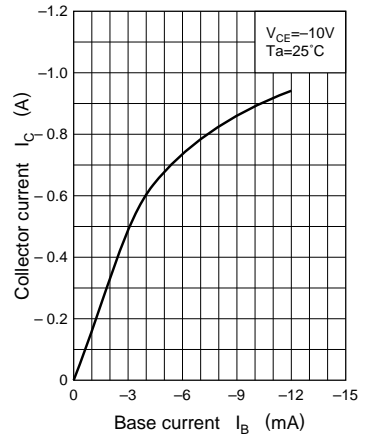
$P_C - T_a$



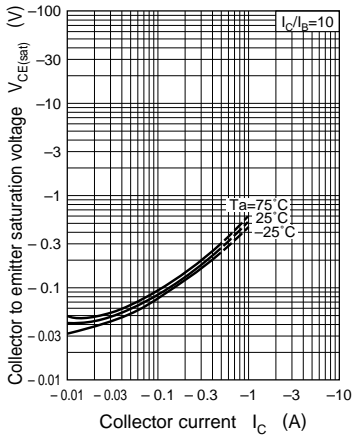
$I_C - V_{CE}$



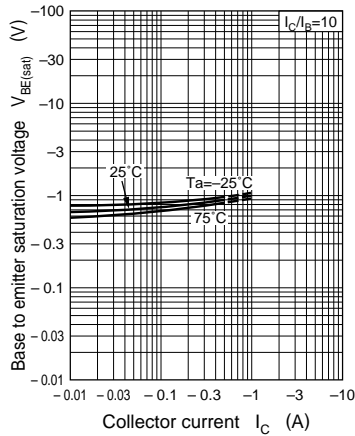
$I_C - I_B$



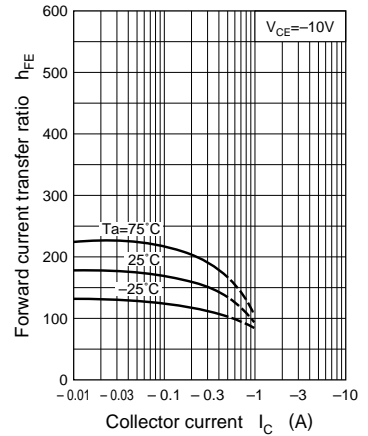
$V_{CE(sat)} - I_C$



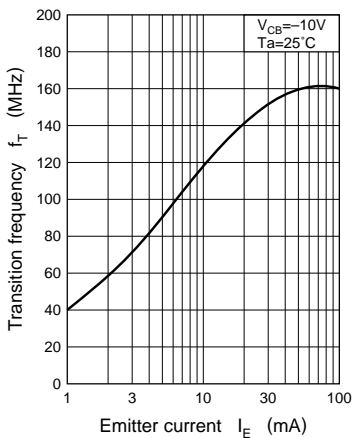
$V_{BE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

